TOSHIBA CMOS Digital Integrated Circuit Silicon Monolithic

TC74VHC4051AF,TC74VHC4051AFT,TC74VHC4051AFK TC74VHC4052AF,TC74VHC4052AFT,TC74VHC4052AFK TC74VHC4053AF,TC74VHC4053AFT,TC74VHC4053AFK

TC74VHC4051AF/AFT/AFK

8-Channel Analog Multiplexer/Demultiplexer

TC74VHC4052AF/AFT/AFK

Dual 4-Channel Analog Multiplexer/Demultiplexer TC74V4053AF/AFT/AFK

Triple 2-Channel Analog Multiplexer/Demultiplexer

The TC74VHC4051A/4052A/4053A are high-speed, low-voltage drive analog multiplexer/demultiplexers using silicon gate CMOS technology. In 3 V and 5 V systems these can achieve high-speed operation with the low power dissipation that is a feature of CMOS.

The TC74VHC4051A/4052A/4053A offer analog/digital signal selection as well as mixed signals. The 4051A has an 8-channel configuration, the 4052A has an 4-channel × 2 configuration, and the 4053A has a 2-channel × 3 configuration.

The switches for each channel are turned ON by the control pin digital signals.

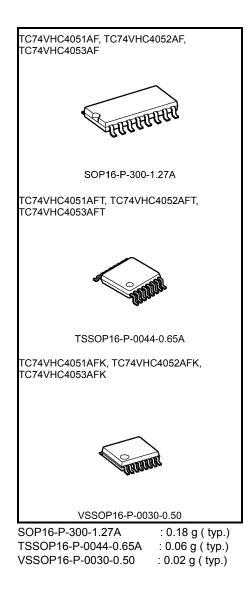
All control inputs are equipped with a newly developed input protection circuit that avoids the need for a diode on the plus side (forward side from the input to the VCC). As a result, for example, 5.5 V signals can be permitted on the inputs even when the power supply voltage to the circuits is off. As a result of this input power protection, the TC74VHC4051A/4052A/4053A can be used in a variety of applications, including in the system which has two power supplies, and in battery backup circuits.

Features

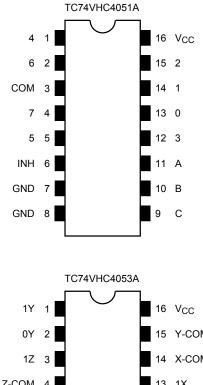
• Low ON resistance: $R_{on} = 45\Omega$ (typ.) (V_{CC} = 3 V)

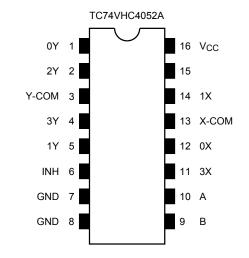
 $R_{on} = 24\Omega$ (typ.) (V_{CC} = 4.5 V)

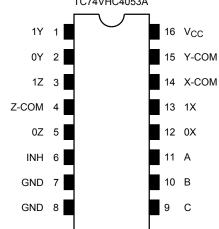
- Low power dissipation: $I_{CC} = 2.0 \ \mu A \ (max) \ (Ta = 25^{\circ}C)$
- Input level: V_{IL} = 0.8V (max) (V_{CC} = 3 V) V_{IH} = 2.0V (min) (V_{CC} = 3 V)
- Power down protection is provided on all control inputs



Pin Assignment (top view)







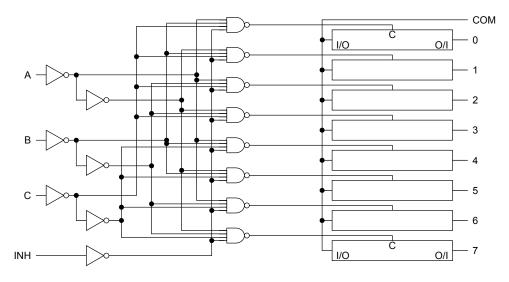
Truth Table

	Contro	l Inputs		"ON" Channel				
Inhibit	C*	В	А	VHC4051A	VHC4051A VHC4052A			
L	L	L	L	0	0X, 0Y	0X, 0Y, 0Z		
L	L	L	Н	1	1X, 1Y	1X, 0Y, 0Z		
L	L	Н	L	2	2X, 2Y	0X, 1Y, 0Z		
L	L	Н	Н	3	3X, 3Y	1X, 1Y, 0Z		
L	Н	L	L	4	—	0X, 0Y, 1Z		
L	Н	L	Н	5	—	1X, 0Y, 1Z		
L	Н	н	L	6	—	0X, 1Y, 1Z		
L	Н	н	Н	7	_	1X, 1Y, 1Z		
Н	Х	Х	Х	None	None	None		

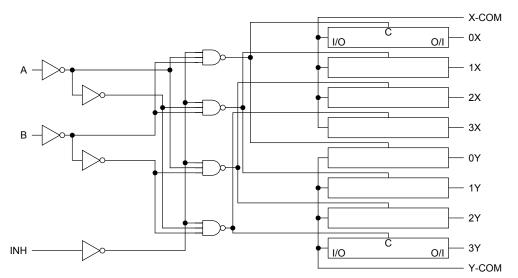
X: Don't care, *: Except VHC4052A

System Diagram

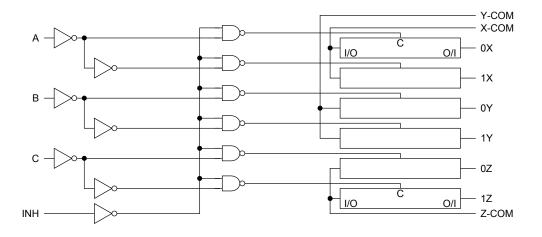
TC74VHC4051A



TC74VHC4052A



TC74VHC4053A



Absolute Maximum Ratings (Note)

Characteristics	Symbol	Rating	Unit
Power supply voltage	V _{CC}	–0.5 to 7.0	V
Control input voltage	V _{IN}	-0.5 to 7.0	V
Switch I/O voltage	V _{I/O}	$-$ 0.5 to V_{CC} + 0.5	V
Input diode current	I _{IK}	-20	mA
I/O diode current	IIOK	±25	mA
Switch through current	Ι _Τ	±25	mA
DC V _{CC} or ground current	ICC	±50	mA
Power dissipation	PD	180	mW
Storage temperature	T _{stg}	–65 to 150	°C

Note : Exceeding any of the absolute maximum ratings, even briefly, may lead to deterioration in IC performance or even destruction.

Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings and the operating ranges.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

Operating Range (Note)

Characteristics	Symbol	Rating	Unit
Power supply voltage	V _{CC}	2 to 5.5	V
Input voltage	V _{IN}	0 to 5.5	V
Switch I/O voltage	V _{I/O}	0 to V _{CC}	V
Operating temperature	T _{opr}	-40 to 85	°C
		0 to 200 (V_{CC} = 2.5 \pm 0.2 V)	
Input rise and fall time	dt/dv	0 to 100 (V_{CC} = 3.3 \pm 0.3 V)	ns/V
		0 to 20 (V_{CC} = 5 \pm 0.5 V)	

Note: The operating ranges must be maintained to ensure the normal operation of the device. Unused control inputs must be tied to either V_{CC} or GND.

Electrical Characteristics

DC Electrical Characteristics

Characteristics		Symbol	Test Condition		٦	Ta = 25°C			$Ta = -40$ to $85^{\circ}C$		
		Symbol	Test Condition	V _{CC} (V)	Min	Тур.	Max	Min	Max	Unit	
		V _{IH}		2.0	1.5			1.5	_	v	
	Liberta Lavrad		—	3.0	2.0			2.0	_		
	High-level			4.5	3.15			3.15	_		
Input voltage				5.5	3.85		_	3.85	_		
input voitage				2.0	_	_	0.5	_	0.5	v	
	Low-level			3.0	_	_	0.8	_	0.8		
	LOW-IEVEI	VIL		4.5	_	_	1.35	_	1.35		
				5.5		_	1.65	_	1.65		
			$V_{IN} = V_{IL} \text{ or } V_{IH}$	V _{IH} 2.3 — 200			_				
		R _{ON}	$V_{I/O} = V_{CC}$ to GND	3.0		45	86		108	Ω	
ON resistance			$I_{I/O} = 2 \text{ mA}$	4.5		24	37	_	46		
ONTESISIANCE			$V_{IN} = V_{IL} \text{ or } V_{IH}$	2.3		28	73	_	84		
			$V_{I/O} = V_{CC}$ or GND	3.0		22	38	_	44		
			$I_{I/O} = 2 \text{ mA}$	4.5	_	17	27	—	31		
Difference of O	N		$V_{IN} = V_{IL} \text{ or } V_{IH}$	2.3		10	25	_	35		
resistance betw		ΔR_{ON}	$V_{I/O} = V_{CC}$ to GND	3.0		5	15	_	20	Ω	
switches			$I_{I/O} = 2 \text{ mA}$	4.5	_	5	13	—	18		
Input/Output lea	akaqe		$V_{OS} = V_{CC}$ or GND								
current	current		$V_{IS} = GND$ to V_{CC}	5.5	—	-	±0.1	—	±1.0	μA	
(switch OFF)			V _{IN} = V _{IL} or V _{IH}								
Input/Output leakage current		lı/O	$V_{OS} = V_{CC}$ or GND	5.5		_	±0.1	_	±1.0	μA	
(switch ON, out	(switch ON, output open)		$V_{IN} = V_{IL} \text{ or } V_{IH}$						•		
Control input cu	ırrent	I _{IN}	$V_{IN} = V_{CC}$ or GND	5.5	—	—	±0.1	—	±1.0	μA	
Quiescent supp	ly current	ICC	$V_{IN} = V_{CC}$ or GND	5.5	—		2.0	—	20.0	μA	

AC Electrical Characteristics (Input: $t_r = t_f = 3 \text{ ns}$)

Ob ana stariatian	O maked	Test Condition		-	Ta = 25°0	C	Ta = -40) to 85°C	Unit		
Characteristics	Symbol			V _{CC} (V)	Min	Тур.	Max	Min	Max	Onic	
		$C_L = 15 \text{ pF}$ $R_L = 1 \text{ k}\Omega$		2.5±0.2		1.2	10	_	16		
				3.3±0.3	—	0.8	6	_	10	ns	
Phase difference	φl/O			5.0±0.5		0.3	4	_	7		
between input and output	φι/Ο	$C_L = 50 \text{ pF}$ $R_L = 1 \text{ k}\Omega$		2.5±0.2		2.6	12	_	18		
				3.3±0.3		1.5	9	_	12		
				5.0±0.5		0.6	6	—	8		
				Eiguro 1	2.5±0.2		3.3	15	_	20	
		$C_L = 15 \text{ pl}$ $R_L = 1 k\Omega$	F	Figure 1	3.3±0.3	_	2.3	11	_	15	ns
Output anable time	t _{pZL}	-			5.0±0.5	_	1.6	7	_	10	
Output enable time	t _{pZH}				2.5±0.2		4.2	25	—	32	
		$C_L = 50 \text{ pF}$ $R_L = 1 \text{ k}\Omega$		Figure 1	3.3±0.3		3.0	18	_	22	
		-			5.0±0.5		2.1	12	—	16	
	t _{pLZ} t _{pHZ}	C _L = 15 pF R _L = 1 kΩ		Figure 1	2.5±0.2		6	15	_	23	ns
					3.3±0.3	—	4.5	11	_	15	
Output dischle time					5.0±0.5		3.2	7	_	10	
Output disable time		$C_L = 50 \text{ pF}$ $R_L = 1 \text{ k}\Omega$		Figure 1	2.5±0.2		9.6	25	—	32	
					3.3±0.3		7.2	18	_	22	
					5.0±0.5		5.1	12	—	16	
Control input capacitance	C _{IN}	All types					3		_	10	pF
		4051A	_	- 0			23.4				
COMMON terminal capacitance	C _{IS}	4052A	Figur	e Z	_	_	13.1	_		_	pF
		4053A					8.2				
		4051A	-	- 0		_	5.7 5.6 —				
SWITCH terminal capacitance	C _{OS}	4052A	Figur	e Z	_			-	—	pF	
		4053A					5.6	.6			
		4051A					0.5				
Feedthrough capacitance	C _{IOS}	4052A	Figure 2		_	—	0.5	_		_	pF
		4053A					0.5				
		4051A	Figure 2 (Note)				15				
Power dissipation capacitance	C _{PD}	4052A			—	_	24	1 —	—	_	pF
		4053A					12				

Note: C_{PD} is defined as the value of the internal equivalent capacitance of IC which is calculated from the operating current consumption without load.

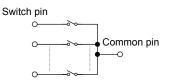
Average operating current can be obtained by the equation:

 $I_{CC \text{ (opr)}} = C_{PD} \cdot V_{CC} \cdot f_{IN} + I_{CC}$

Analog Switch Characteristics (Ta = 25°C) (Note)

Characteristics	Test Condition		Тур.	Unit	
		$V_{CC}(V)$	51		
Sine Wave Distortion (T.H.D)	$R_L = 10 \text{ k}\Omega, C_L = 50 \text{ pF},$	$V_{IN}=2.0 \ V_{p\text{-}p}$	3.0	0.1	%
Sine wave bistoriion (1.11.b)	f _{IN} = 1 kHz	$V_{IN}=4.0 \ V_{p\text{-}p}$	4.5	0.03	70
	V _{IN} is centered at (V _{CC} /2).	4051A		150	
	Adjust input for 0dBm.	4052A	3.0	200	
Frequency response	Increase f _{IN} frequency until dB meter	4053A		240	MHz
(switch ON)	reads –3dB.	4051A		180	
	$R_L = 50 \ \Omega, \ C_L = 10 \ pF$,sine wave	4052A	4.5	230	
	Figure 3	4053A		280	
	V _{IN} is centered at (V _{CC} /2).	3.0	-45		
	Adjust input for 0dBm.				
Feed through attenuation	R_L = 600 $\Omega,~C_L$ = 50 pF, f_{IN} = 1 MHz, s				
(switch OFF)	Figure 4	4.5	-45	dB	
	R _I = 50 Ω, C _I = 10 pF, f _{IN} = 1 MHz, si	3.0	-65		
		4.5	-65		
Crosstalk	R_L = 600 $\Omega,~C_L$ = 50 pF, f_{IN} = 1 MHz, s	3.0	60		
(control input to signal output)	$(t_r = t_f = 6 \text{ ns})$			mV	
	Figure 5	4.5	100		
Crosstalk	$V_{\mbox{IN}}$ is centered at (V_{CC}/2). Adjust input	3.0	-45		
(between any switches)	R_L = 600 $\Omega,~C_L$ = 50 pF, f_{IN} = 1 MHz, s	4.5	-45	dB	
(between any switches)	Figure 6		-40		

Note: These characteristics are determined by design of devices.



AC Test Circuit

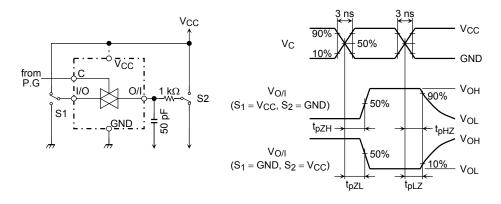


Figure 1 t_{pLZ} , t_{pHZ} , t_{pZL} , t_{pZH}

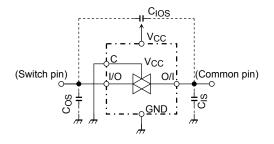
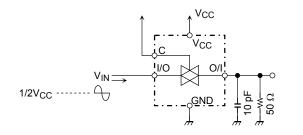


Figure 2 C_{IOS}, C_{IS}, C_{OS}





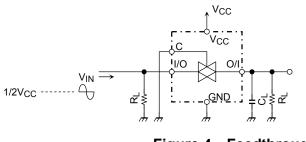
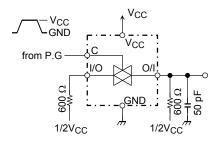
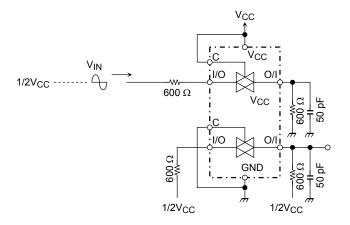
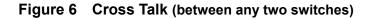


Figure 4 Feedthrough





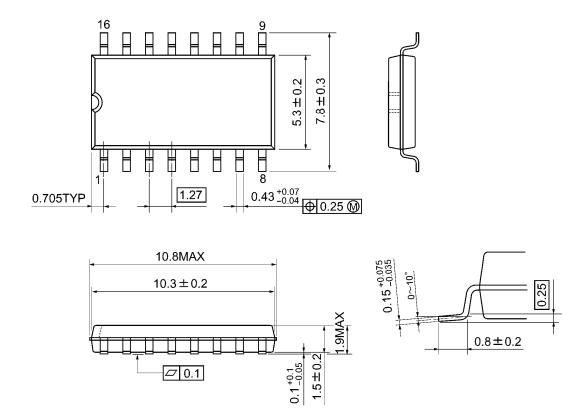




Package Dimensions

SOP16-P-300-1.27A

Unit: mm

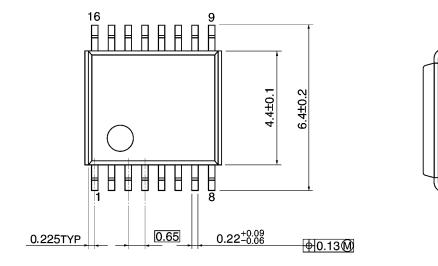


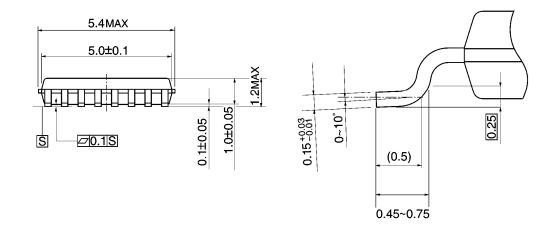
Weight: 0.18 g (typ.)

Package Dimensions

TSSOP16-P-0044-0.65A

Unit: mm



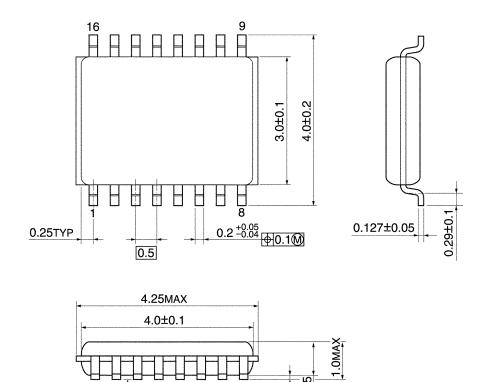


Weight: 0.06 g (typ.)

Package Dimensions

VSSOP16-P-0030-0.50

Unit: mm



☑0.1

0.1±0.05 0.8±0.05

Weight: 0.02 g (typ.)

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20070701-EN GENERAL

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